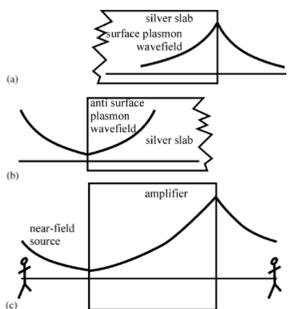


Near-Field Enhancement Using Uniaxial Wire Medium With Impedance Loadings

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Background and Motivation

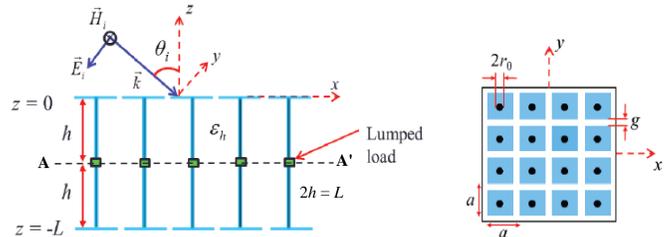


- ✓ The amplification process is due to the excitation of **surface plasmon resonances** on the surfaces of the slab
- ✓ “**Spoof plasmons**” as strongly localized surface waves are due to resonant interaction of the electromagnetic field and the charge density oscillations in metals

J. B. Pendry and S. A. Ramakrishna, *Physica B*, 338, 329-332, 2003

Bi-Layer Mushroom Structure

Analytical Model



Reflection and Transmission Coefficients

Reflection coefficient for the even excitation (PEC symmetry)

$$R_{\text{even}} = \frac{(jk_0 - \eta_0 \gamma_0 Y_g) K - jk_0 \gamma_0 M}{(jk_0 + \eta_0 \gamma_0 Y_g) K + jk_0 \gamma_0 M}$$

where

$$K = \gamma_{\text{TM}} \sinh(\gamma_{\text{TM}} h) \cos(k_{\text{TEM}} h) - k_{\text{TEM}} \sin(k_{\text{TEM}} h) \times \left[\left(\frac{\epsilon_h}{\epsilon_{\text{TM}}} - 1 \right) \cosh(\gamma_{\text{TM}} h) + \frac{\epsilon_h \gamma_{\text{TM}} \sinh(\gamma_{\text{TM}} h)}{\epsilon_{\text{TM}} j \omega C Z_{\text{Load,eff}}} \right]$$

$$M = 2 \left(\epsilon_h - \epsilon_{\text{TM}}^{\text{TM}} \right) + \cosh(\gamma_{\text{TM}} h) \left[\frac{j \epsilon_h k_{\text{TEM}}}{\omega C Z_{\text{Load,eff}}} \sin(k_{\text{TEM}} h) + \left(\epsilon_h \left(\frac{\epsilon_h}{\epsilon_{\text{TM}}} - 2 \right) + 2 \epsilon_{\text{TM}}^{\text{TM}} \right) \cos(k_{\text{TEM}} h) \right] + \left(\epsilon_h - \epsilon_{\text{TM}}^{\text{TM}} \right) \sinh(\gamma_{\text{TM}} h) \left[\left(\frac{\gamma_{\text{TM}}}{\gamma_{\text{TM}}} + \frac{\gamma_{\text{TM}}}{\gamma_{\text{TM}}} \right) j \sin(k_{\text{TEM}} h) + \frac{\epsilon_h \gamma_{\text{TM}}}{\epsilon_{\text{TM}} j \omega C Z_{\text{Load,eff}}} \cos(k_{\text{TEM}} h) \right]$$

C. S. R. Kaipa, et al., *IEEE AWPL*, 10, 1503, 2011

$$\gamma_0 = \sqrt{k_z^2 - k_0^2}, \quad k_z = k_0 \sin \theta_i, \quad \gamma_{\text{TM}} = \sqrt{k_p^2 + k_z^2 - k_0^2 \epsilon_h}, \quad \gamma_{\text{TEM}} = jk_{\text{TEM}} = jk_0 \sqrt{\epsilon_h}$$

$$\epsilon_{\text{TM}}^{\text{TM}} = \epsilon_h k_p^2 / (k_p^2 + k_z^2), \quad k_p = \sqrt{(2\pi/a)^2 / \log[a^2/4r_0(a-r_0)]}$$

Grid admittance of the patch array $Y_g = j(\epsilon_h + 1)(k_0 a / \eta_0 \pi) \log[\csc(\pi g / 2a)]$

Capacitance per unit length of the wire medium $C = 2\pi \epsilon_h \epsilon_0 / \log[a^2/4r_0(a-r_0)]$

Effective load impedance $Z_{\text{Load,eff}} = j\omega L_{\text{par}} + \frac{1}{(j\omega C_{\text{par}} + 1/Z_{\text{Load}})}$

Parasitic capacitance C_{par} Parasitic inductance L_{par}

Z_{Load} Impedance of the lumped load (inductive/capacitive)

Reflection coefficient for the odd excitation (PMC symmetry)

$$R_{\text{odd}} = -\frac{\frac{\epsilon_h k_x^2 \tanh(\gamma_{\text{TM}} h)}{\gamma_{\text{TM}}(k_x^2 + k_p^2)} + \frac{\epsilon_h k_p^2 \tan(k_{\text{TEM}} h)}{k_{\text{TEM}}(k_x^2 + k_p^2)} - \left(\frac{1}{\gamma_0} + j \frac{Y_g \eta_0}{k_0} \right)}{\frac{\epsilon_h k_x^2 \tanh(\gamma_{\text{TM}} h)}{\gamma_{\text{TM}}(k_x^2 + k_p^2)} + \frac{\epsilon_h k_p^2 \tan(k_{\text{TEM}} h)}{k_{\text{TEM}}(k_x^2 + k_p^2)} + \left(\frac{1}{\gamma_0} - j \frac{Y_g \eta_0}{k_0} \right)}$$

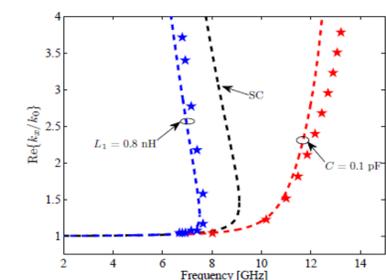
Yakovlev et al., *3rd Int. Congress on Advan. Electromag. Materi. in Microwa. and Optic.*, (2009)

Reflection and Transmission coefficients for the bi-layer mushroom structure

$$R = \frac{1}{2} (R_{\text{even}} + R_{\text{odd}})$$

$$T = \frac{1}{2} (R_{\text{even}} - R_{\text{odd}})$$

Dispersion Behavior of the Guided Modes

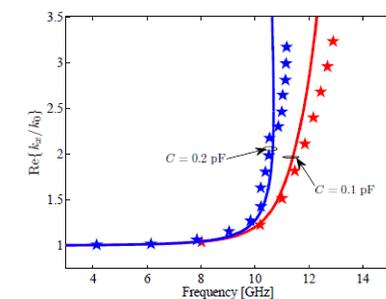


$a = 2 \text{ mm}$
 $g = 0.2 \text{ mm}$
 $r_0 = 0.05 \text{ mm}$
 $L = 2 \text{ mm}$
 $\epsilon_h = 10.2$
 $C_{\text{par}} = 0.02 \text{ pF}$
 $L_{\text{par}} = 0.06 \text{ nH}$

Dashed lines: Analytical model
Symbols: HFSS

- ✓ Reduction of the resonant frequency with **inductive loads** and decrease of the effective plasma frequency
- ✓ Increase of resonant frequency with **capacitive loads**

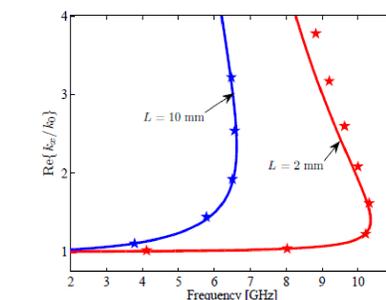
- ✓ Flat dispersion with **capacitive loads**



$a = 2 \text{ mm}$
 $g = 0.2 \text{ mm}$
 $r_0 = 0.05 \text{ mm}$
 $L = 2 \text{ mm}$
 $\epsilon_h = 10.2$
 $C_{\text{par}} = 0.02 \text{ pF}$
 $L_{\text{par}} = 0.06 \text{ nH}$

Solid lines: Analytical model
Symbols: HFSS

- ✓ Flat dispersion with **capacitive loads**



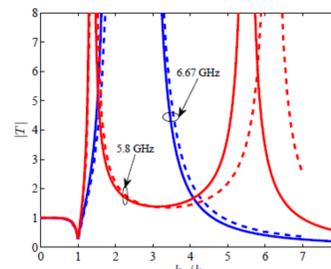
$a = 2 \text{ mm}$
 $g = 0.2 \text{ mm}$
 $r_0 = 0.05 \text{ mm}$
 $L_1 = 5 \text{ nH}$
 $\epsilon_h = 1$

Solid lines: Analytical model
Symbols: HFSS

- ✓ Increasing L/a results in a lower resonant frequency and in an enhancement of the normalized propagation constant $\text{Re}\{k_x/k_0\}$

Imaging with Inductive Loadings

Amplification of evanescent waves



$a = 2 \text{ mm}$
 $g = 0.2 \text{ mm}$
 $r_0 = 0.05 \text{ mm}$
 $L_1 = 5 \text{ nH}$
 $L = 10 \text{ mm}$
 $\epsilon_h = 1$

Solid lines: Analytical model
Dashed lines: CST

- ✓ Strong amplification of the near field for the wave vector components in the range $1 < k_x/k_0 < 4$ at the frequency of 6.67 GHz

Imaging a line source

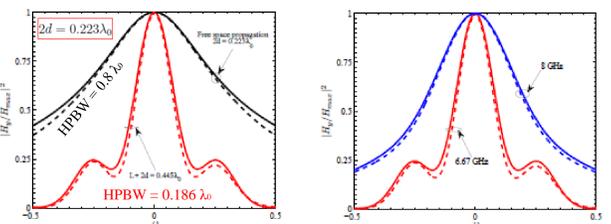
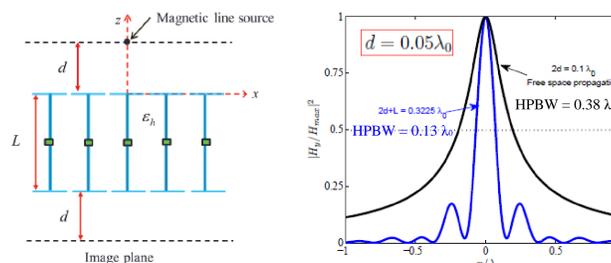
$$\mathbf{J}_{\text{ms}} = \hat{\mathbf{y}} I_0 \delta(z-d) \delta(x)$$
 Current density of the magnetic line source

$$\mathbf{H}(x, z) = \hat{\mathbf{y}} \frac{I_0 k_0^2}{j \omega \mu_0 \pi} \left[\frac{1}{4j} H_0^{(2)}(k_0 \rho) \right]$$
 Incident magnetic field

Magnetic field at the image plane (distance d from the lower interface of the structure) as a Sommerfeld-type integral

$$H_y(x) = \frac{I_0 k_0^2}{j \omega \mu_0 \pi} \int_0^\infty \frac{1}{2\gamma_0} e^{-\gamma_0(2d)} T(\omega, k_x) \cos(k_x x) dk_x$$

$f = 6.67 \text{ GHz}$

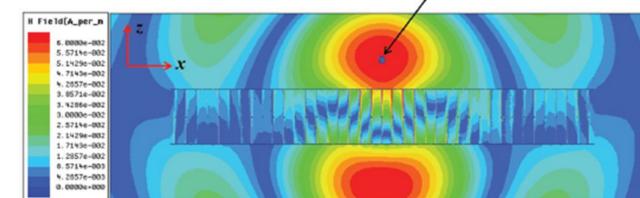


Solid lines: Analytical model
Dashed lines: HFSS

- ✓ Resolution of the bi-layer mushroom lens is $\lambda/6$

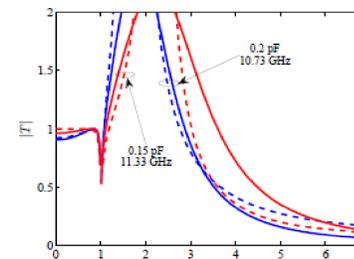
Magnetic field distribution of the inductively loaded bi-layer mushroom structure: HFSS simulation results

$f = 6.67 \text{ GHz}$ $d = 5 \text{ mm}$ $W_x = 39a \approx 1.8 \lambda_0$ Magnetic line source



Imaging with Capacitive Loadings

Amplification of evanescent waves

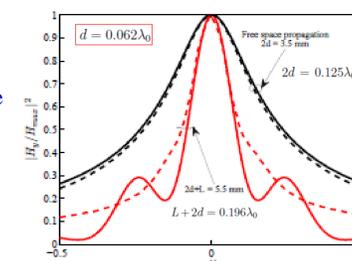


$a = 2 \text{ mm}$
 $g = 0.2 \text{ mm}$
 $r_0 = 0.05 \text{ mm}$
 $L = 2 \text{ mm}$
 $\epsilon_h = 10.2$
 $C_{\text{par}} = 0.02 \text{ pF}$
 $L_{\text{par}} = 0.06 \text{ nH}$

Solid lines: Analytical model
Dashed lines: CST

- ✓ Strong amplification of the near field

Imaging a line source



Capacitive loading of 0.2 pF

Distance
Free space propagation 3.5 mm
With structure 5.5 mm
Homogenization results
 $f = 10.73 \text{ GHz}$
HPBW
Free space propagation $0.47 \lambda_0$
With structure $0.16 \lambda_0$

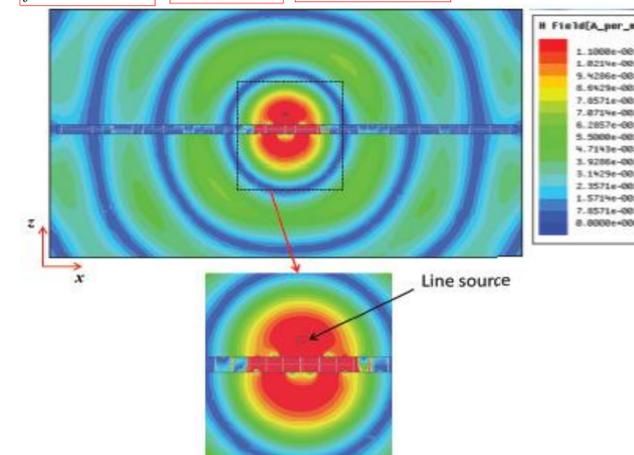
Simulation results
 $f = 11.27 \text{ GHz}$

HPBW
Free space propagation $0.47 \lambda_0$
With structure $0.19 \lambda_0$

- ✓ Resolution of the bi-layer mushroom lens is $\lambda/6$

Magnetic field distribution of the capacitively loaded bi-layer mushroom structure: HFSS simulation results

$f = 11.27 \text{ GHz}$ $d = 1.75 \text{ mm}$ $W_x = 35a \approx 2.65 \lambda_0$



Conclusions

- We demonstrate the possibility of achieving **evanescent-wave enhancement** and **near-field imaging** by using a bi-layer mushroom structure with capacitively/inductively loaded metallic wires
- **Strong interaction** of two metallic grids, coupled by an array of metallic wires
- In the case of capacitive loadings, a **flat dispersion** for the guided modes can be obtained with a sub-wavelength design based on a high-dielectric constant
- Long vias loaded with lumped inductors are used for a sub-wavelength design with a low-dielectric constant